

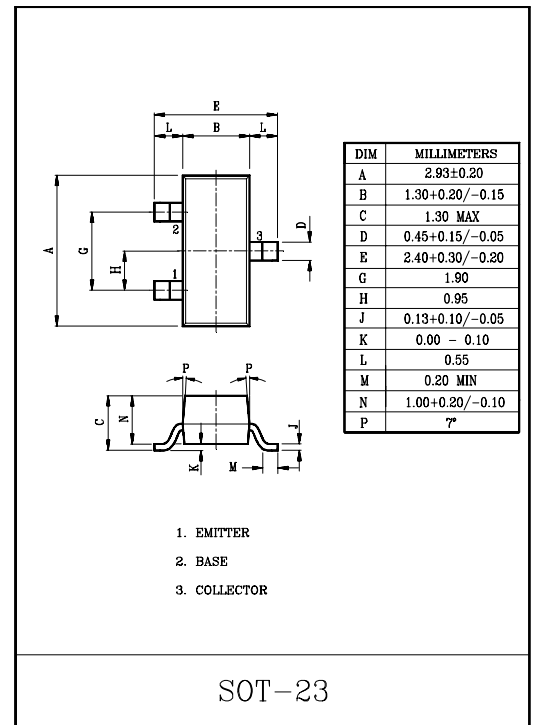
GENERAL PURPOSE APPLICATION.
SWITCHING APPLICATION.

• For Complementary with NPN Type BC849/850

MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	BC859	-30	V
	BC860	-50	
Collector-Emitter Voltage	BC859	-30	V
	BC860	-45	
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Current	I _C	-100	mA
Collector Power Dissipation	P _C *	350	mW
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	-55~150	°C

P_C* : Package Mounted On 99.5% Alumina 10×8×0.6mm.



ELECTRICAL CHARACTERISTICS (Ta=25°C)

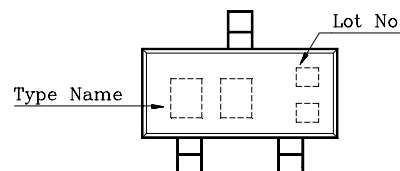
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector-Emitter Breakdown Voltage	BC859	I _C =-10mA, I _B =0	-30	-	-	V
	BC860		-45	-	-	
Collector-Base Breakdown Voltage	BC859	I _C =-10μA, I _E =0	-30	-	-	V
	BC860		-50	-	-	
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	I _E =-10μA, I _C =0	-5	-	-	V
Collector Cut-off Current	I _{CBO}	V _{CB} =-30V, I _E =0	-	-	-15	nA
DC Current Gain	h _{FE}	I _C =-2mA, V _{CE} =-5V	125	-	475	
Base-Emitter Voltage	V _{BE(ON) 1}	I _C =-2mA, V _{CE} =-5V	-0.6	-0.65	-0.75	V
	V _{BE(ON) 2}	I _C =-10mA, V _{CE} =-5V	-	-	-0.82	
Collector-Emitter Saturation Voltage	V _{CE(sat) 1}	I _C =-10mA, I _B =-0.5mA	-	-0.075	-0.3	V
	V _{CE(sat) 2}	I _C =-100mA, I _B =-5mA	-	-0.25	-0.65	
Base-Emitter Saturation Voltage	V _{BE(sat) 1}	I _C =-10mA, I _B =-0.5mA	-	-0.7	-	V
	V _{BE(sat) 2}	I _C =-100mA, I _B =-5mA	-	-0.85	-	
Transition Frequency	f _T	I _C =-10mA, V _{CE} =-5V, f=100MHz	-	150	-	MHz
Collector Output Capacitance	C _{ob}	V _{CB} =-10V, I _E =0, f=1MHz	-	4.5	-	pF
Noise Figure	NF	I _C =-200μA, V _{CE} =-5V R _g =10kΩ, f=1kHz	-	-	4.0	dB

Note : h_{FE} Classification A:125~250, B:220~475

MARK SPEC

TYPE	BC859A	BC859B	BC860A	BC860B
MARK	4A	4B	4E	4G

Marking



BC859/860

